

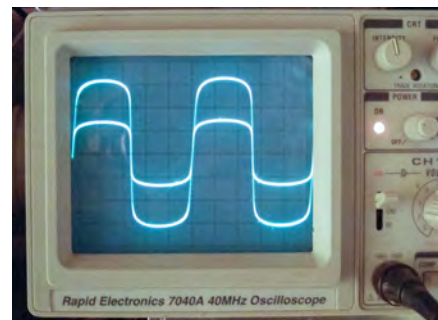
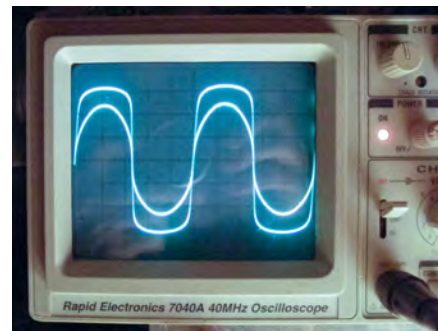
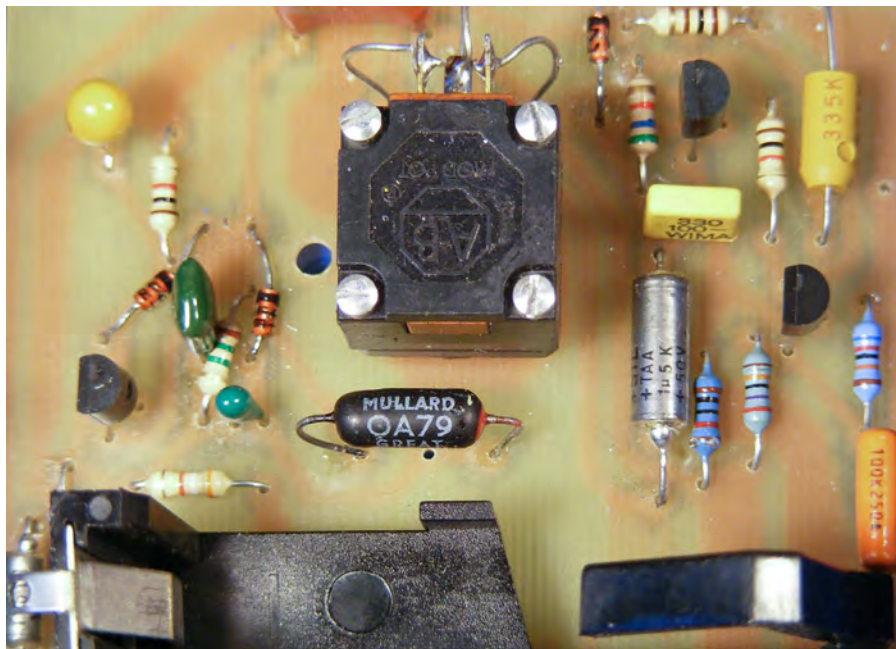


Fig.3. The earliest mass-produced semiconductor, the point-contact diode. Here, a 1960 OA79 is used in a Colorsound Single Knob Fuzz effects box, along with a silicon diode to give asymmetrical clipping action.

on the market, such as those by Chandler Ltd. There is renewed interest in germanium for heterojunction bipolar transistors where germanium is combined with silicon in the base region of the device. They are used in very low-noise microwave applications.

Germanium vs silicon

The first mass-produced semiconductors were germanium point-contact diodes, such as the OA81 and OA79. I use OA79s in the latest version of my Colorsound Single Knob fuzz box, see Fig.3. These large-case glass SO-25 types were then miniaturised down to the DO-7 glass-case OA91 and AA119 devices. There is also a popular US germanium diode, the 1N60, which is still available, albeit at high cost, from companies such as Tayda. Their advantage is the low turn-on voltage of around 0.25V and their 'soft knee', the point where forward conduction begins. It gives a 'soft' distortion when used for fuzz boxes. They are also still the most sensitive device for crystal sets (although gallium-arsenide types can have a lower forward voltage). Today, these are often replaced by the more consistent schottky diodes, such as the BAT42, but to a discerning guitarist, nothing sounds quite as good

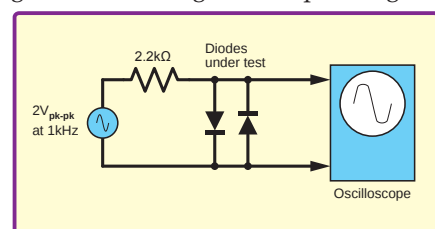


Fig.4. Clipping circuit to test different diodes

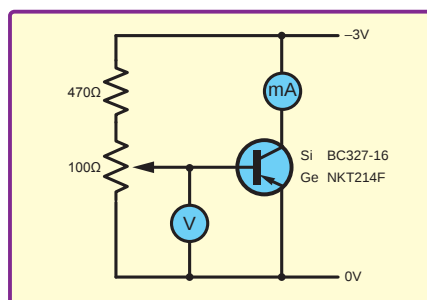


Fig.6. Transistor test circuit to compare the transconductance (base voltage vs collector current) of germanium and silicon transistors

as selected germanium devices. (I find musician's ears are finely tuned to distortion changes with level). Fig.4 shows a clipping circuit using various diodes. The resulting waveforms are shown in Fig.5.

With transistors, guitarists can also hear the differences between germanium and silicon. You can't 'see' it on a

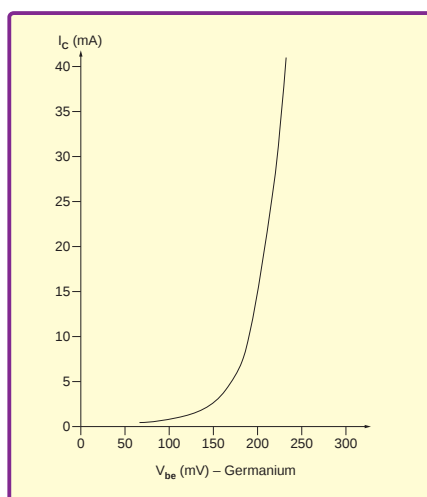


Fig.7. Germanium transconductance curve

Fig.5. Clipping waveforms of various diodes. (Top) 1N4148 silicon compared to OA91 germanium, note the more rounded shape and lower amplitude of the germanium diodes. (Bottom) Comparison of silicon with BAT42 schottky diodes – the schottky diodes have lower amplitude, reflecting their lower forward voltage drop

'scope, but open-loop (with no negative feedback) they are supposedly more linear than silicon, reputedly having a less abrupt turn-on. Being a born sceptic, I distrusted the curves given in previous articles and amplifier books, so plotted my own, using the test circuit in Fig.6. This resulted in the collector current (I_c) vs base voltage (V_{be}) or transconductance curves given in Fig.7

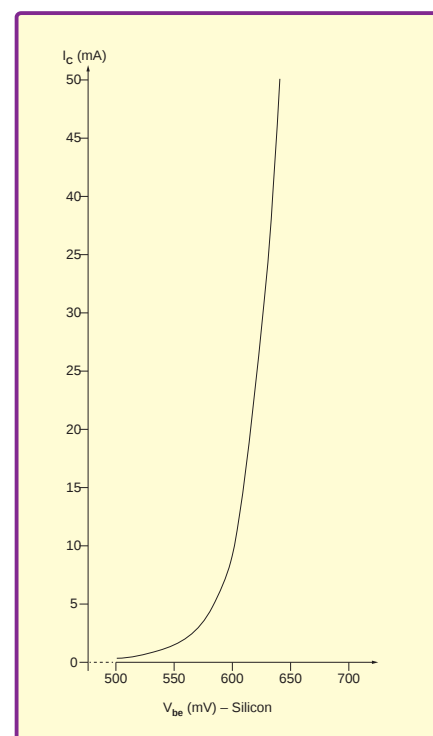


Fig.8. Silicon transconductance curve

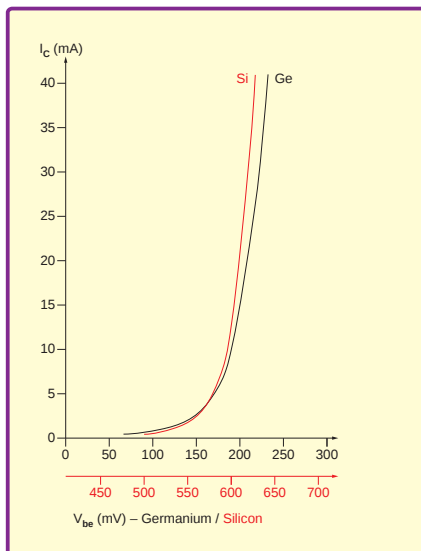


Fig.9. Comparison of silicon vs germanium transconductance curves

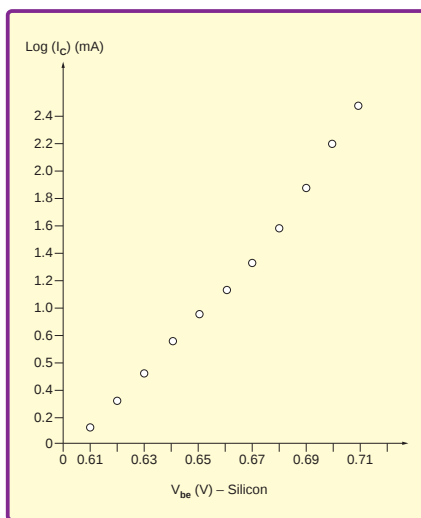


Fig.10. Logarithm of collector current vs base-emitter voltage gives a straight line with silicon. Germanium is the same but slope drifts badly with temperature.

and Fig.8. Using typical germanium and silicon audio 'driver' transistors (NKT214F and BC327), I found the germanium 'knee' to be only slightly softer. Overlaying the curves to take into account the different threshold voltages shows the difference in Fig.9. Both curves follow the usual logarithmic increase in I_C with increasing V_{be} in accordance with the physics of normal bipolar transistor action. I started to plot this, logging the current to see if I got a straight line, which I did (Fig.10) although I did feel like I was back at school! (As an aside, it was the improved stability of silicon transistors that allowed proper logarithmic signal conversion, which paved the way for Moog's analogue synthesiser.)

The Bailey amplifier

In November 1966, AR Bailey published a transformer-driven class AB Hi-Fi amplifier in *Wireless World*. It had low total harmonic distortion and it

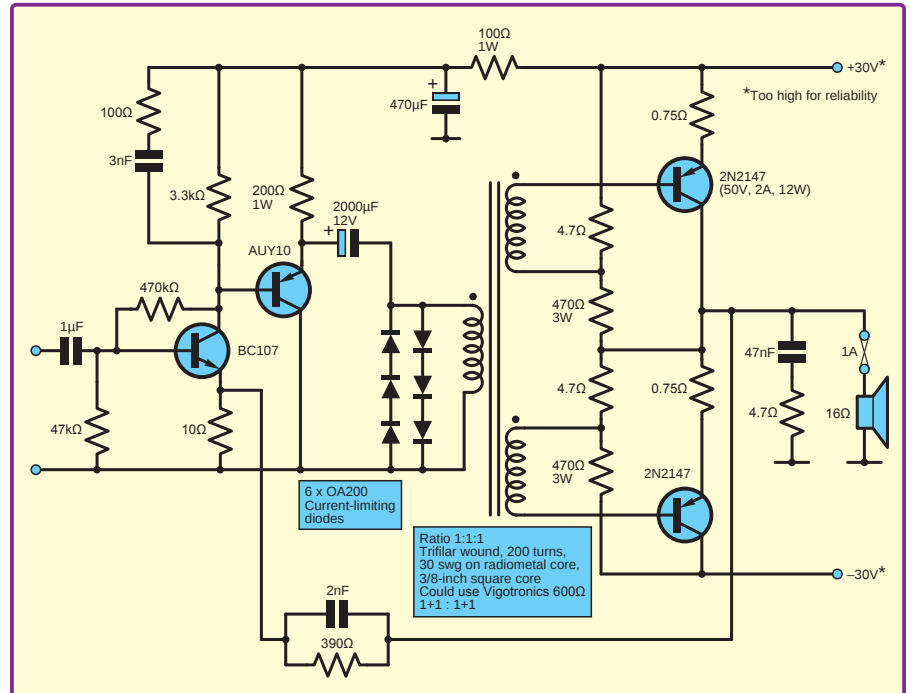


Fig.11. AR Bailey's 1966 transistor power amplifier used a driver transformer to give phase splitting and deal with leakage currents. Distortion was much worse with silicon transistors.

used germanium, not silicon transistors (see Fig.11). Then, in November 1969, John Linsley-Hood published another amplifier in *Wireless World*, and he also found lower distortion with germanium transistors in a standard common-emitter amplifier (Fig.12). (I tried but couldn't replicate this result. His circuit seemed to clip softer, rounding off square waves, but I suspect this was due to high internal feedback capacitances. Of course, the higher open-loop gain obtained with multiple silicon transistors, means silicon distortion can be made much lower when high negative feedback is applied.)

Germanium Hi-Fi

The first transformerless Hi-Fi amplifier was germanium-based, developed by HC Lin at RCA in 1956. It used a quasi-complementary output stage with a single low-power NPN device, the rare 2N35 – see Fig.13. The elimination of audio transformers was essential to allow high levels of negative feedback and the consequent reduction of distortion. Later, this circuit was developed by Toby and Dinsdale for a constructor's version in *Wireless World* in 1961. It was actually a rehash of a Lin-derived guided missile servo amplifier they had designed earlier, which they found also sounded rather good! The single NPN, now a 2N388A, again caused sourcing problems, with

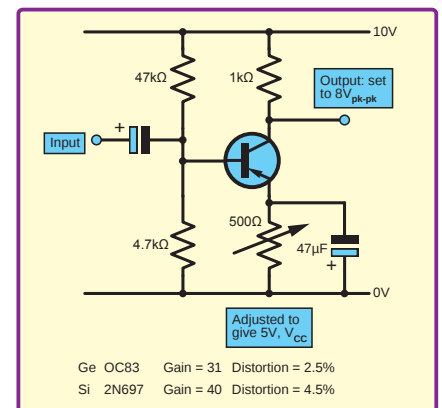


Fig.12. Common-emitter amp for comparing silicon and germanium transistors.

the only UK NPN device available at the time – the OC140 – tending to blow up. Later, Mullard produced the AC127Z, a selected AC127, which had sufficient V_{ce} rating.

That's all we have space for this month – more on *Ge-mania* in the next issue!

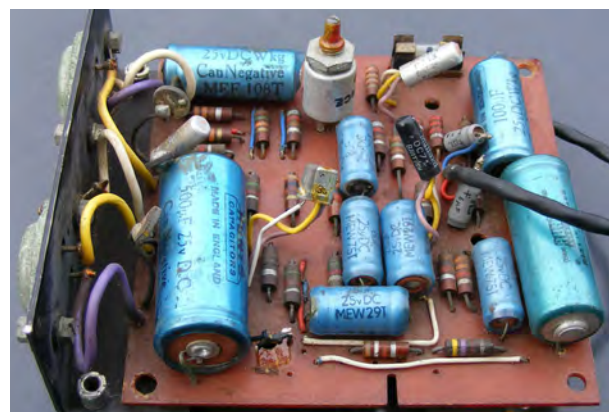


Fig.13. Power amplifier based on the Lin design from the early 1960s. The three-lead 2N35 in the silver can (dead centre) was one of the first NPN germanium transistors, allowing elimination of transformers in amplifiers.